

		Room A (Monterosso, B1F)	Room B (Vernazza, 3F)	Room C (Forum 1, 3F)	Room D (Forum 2, 3F)	Lobby
October 13 (SUN)						
13:30-14:30	60'	[Short Courses 1] Prof. Bernard Gil (CNRS-Univ. of Montpellier, France) "Current Status Regarding Discriminative Optical Properties of Various BN Polytypes"				
14:30-15:30	60'	[Short Courses 2] Prof. Dong-Pyo Han (Pukyong Nat'l Univ., Korea) "Small-Signal Analysis as a Useful Tool to Investigate the Nature of III-Nitride Semiconductor Light-Emitting Devices"				
15:30-15:50	20'	Coffee Break				
15:50-18:00	130'	[Short Courses 3] Prof. Soon-Ku Hong (Chungnam Nat'l Univ., Korea) "Structural Defects in SiC Bulk and Epilayers"				
18:30-20:00	90'	Welcome Reception (Blue Seagull, 2F)				
October 14 (MON)						
09:00-09:20	20'	Opening Ceremony (Monterosso, B1F)				
09:20-10:00	40'	[Plenary Session 1] Prof. Hao-Chung Kuo (Nat'l Yang Ming Chiao Tung Univ., Taiwan) "GaN Micro-LED Array for Chip-to-Chip Interconnection" (Monterosso, B1F)				
10:00-10:40	40'	[Plenary Session 2] Prof. Suda Jun (Nagoya Univ., Japan) "Vertical GaN Power Devices on GaN Substrates" (Monterosso, B1F)				
10:40-11:00	20'	Coffee Break				
11:00-12:25	85'	[MA1] Symposium GL: III-N Materials and Lighting Devices (1/7)	[MB1] Symposium GE: III-N Materials and Electronic Devices (1/7) <i>(11:00-12:30)</i>	[MC1] Symposium SiC: SiC Materials and Devices (1/4)		Registration & Exhibition
12:25-13:45	80'	Lunch (Blue Seagull, 2F)				
13:45-15:55	130'	[MA2] Symposium GL: III-N Materials and Lighting Devices (2/7) <i>(13:45-15:40)</i>	[MB2] Symposium GE: III-N Materials and Electronic Devices (2/7) <i>(13:45-16:00)</i>	[MC2] Symposium SiC: SiC Materials and Devices (2/4) <i>(13:45-15:50)</i>		
15:55-16:15	20'	Coffee Break				
16:15-18:30	135'	[MA3] Symposium GL: III-N Materials and Lighting Devices (3/7)	[MB3] Symposium GE: III-N Materials and Electronic Devices (3/7)	[MC3] Symposium SiC: SiC Materials and Devices (3/4) <i>(16:15-18:05)</i>		
October 15 (TUE)						
09:00-09:40	40'	[Plenary Session 3] Prof. Bo Shen (Peking Univ., China) "Recent Progress on the Large Lattice Mis-Matched Epitaxial Growth and Defect Control of III-Nitride Semiconductors" (Monterosso, B1F)				
09:40-10:00	20'	Coffee Break				
10:00-12:15	135'	[TA1] Special Session: BN Materials and Devices (1/3)	[TB1] Symposium GE: III-N Materials and Electronic Devices (4/7)	[TC1] Symposium SiC: SiC Materials and Devices (4/4) <i>(10:00-11:35)</i>		Registration & Exhibition
12:15-13:35	80'	Lunch (Blue Seagull, 2F)				
13:35-15:10	95'	[TA2] Special Session: BN Materials and Devices (2/3)	[TB2] Symposium GE: III-N Materials and Electronic Devices (5/7)	[TC2] Symposium GaO: Ga ₂ O ₃ Materials and Electronic Devices (1/6) <i>(13:35-15:15)</i>	[TD1] Wide-Bandgap Semiconductor Quantum Devices 1 <i>(13:35-15:15)</i>	
15:10-15:30	20'	Coffee Break				
15:30-16:55	85'	[TA3] Special Session: BN Materials and Devices (3/3) <i>(15:30-16:40)</i>	[TB3] Symposium GE: III-N Materials and Electronic Devices (6/7) <i>(15:30-17:00)</i>	[TC3] Symposium GaO: Ga ₂ O ₃ Materials and Electronic Devices (2/6) <i>(15:30-16:50)</i>	[TD2] Wide-Bandgap Semiconductor Quantum Devices 2 <i>(15:30-16:35)</i>	
16:55-17:00	05'	Break				
17:00-18:25	85'	[TA4] Symposium GL: III-N Materials and Lighting Devices (4/7) <i>(17:00-18:10)</i>	[TB4] Symposium GE: III-N Materials and Electronic Devices (7/7) <i>(17:00-18:35)</i>	[TC4] Symposium GaO: Ga ₂ O ₃ Materials and Electronic Devices (3/6) <i>(17:00-17:50)</i>	[TD3] Novel Devices <i>(17:00-17:45)</i>	
October 16 (WED)						
09:00-10:40	100'	[WA1] Symposium GL: III-N Materials and Lighting Devices (5/7) <i>(09:00-10:50)</i>	[WB1] Symposium GaO: Ga ₂ O ₃ Materials and Electronic Devices (4/6)	[WC1] Special Session: Diamond Materials and Devices (1/3)		Registration & Exhibition
10:40-11:00	20'	Coffee Break				
11:00-12:20	80'	[WA2] Symposium GL: III-N Materials and Lighting Devices (6/7)	[WB2] Symposium GaO: Ga ₂ O ₃ Materials and Electronic Devices (5/6)	[WC2] Special Session: Diamond Materials and Devices (2/3)		
12:20-13:40	80'	Lunch (Blue Seagull, 2F)				
13:40-17:15	215'	[WA3] Symposium GL: III-N Materials and Lighting Devices (7/7)	[WB3] Symposium GaO: Ga ₂ O ₃ Materials and Electronic Devices (6/6) <i>(13:40-15:05)</i>	[WC3] Special Session: Diamond Materials and Devices (3/3) <i>(13:40-15:00)</i>		
17:15-18:30	-	Break (Move to the Banquet Place)				
18:30-20:30	120'	Banquet (The Westin Josun Busan)				

October 17 (THU)			
09:00-10:30	90'	Poster Session 1 (Vernazza, 3F) & Poster Session 2 (Forum 1, 3F)	Registration & Exhibition
10:30-10:50	20'	Coffee Break	
10:50-11:30	40'	[Plenary Session 4] Prof. Debdeep Jena (Cornell Univ., USA) "New Discoveries that are Unleashing Ultrawide Bandgap Semiconductor Electronics" (Monterosso, B1F)	
11:30-12:10	40'	[Plenary Session 5] CTO Samuel Cho (RFHIC, Korea) "GaN Device-Based Radio Frequency and Microwave Technology" (Monterosso, B1F)	
12:10-12:20	10'	Award & Closing Ceremony (Monterosso, B1F)	